

54F/74F563 Octal D-Type Latch with TRI-STATE® Outputs

General Description

The 'F563 is a high-speed octal latch with buffered common Latch Enable (LE) and buffered common Output Enable $(\overline{\text{OE}})$ inputs.

This device is functionally identical to the 'F573, but has inverted outputs.

Features

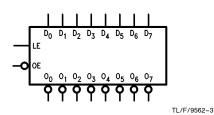
- Inputs and outputs on opposite sides of package allowing easy interface with microprocessors
- Useful as input or output port for microprocessors
- Functionally identical to 'F573

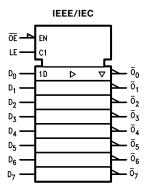
Commercial	Military	Package Number	Package Description		
74F563PC		N20A	20-Lead (0.300" Wide) Molded Dual-In-Line		
	54F563DM (Note 2)	J20A	20-Lead Ceramic Dual-In-Line		
74F563SC (Note 1)		M20B	20-Lead (0.300" Wide) Molded Small Outline, JEDEC		
74F563SJ (Note 1)		M20D	20-Lead (0.300" Wide) Molded Small Outline, EIAJ		
	54F563FM (Note 2)	W20A	20-Lead Cerpack		
	54F563LM (Note 2)	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C		

Note 1: Devices also available in 13" reel. Use suffix = SCX and SJX.

Note 2: Military grade device with environmental and burn-in processing. Use suffix = DMQB, FMQB and LMQB.

Logic Symbols





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Unit Loading/Fan Out

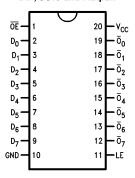
		54F/74F			
Pin Names Description		U.L. HIGH/LOW	Input I _{IH} /I _{IL} Output I _{OH} /I _{OL}		
D ₀ -D ₇ LE OE	Data Inputs Latch Enable Input (Active HIGH) TRI-STATE Output Enable Input (Active LOW)	1.0/1.0 1.0/1.0 1.0/1.0	20 μ A/ $-$ 0.6 mA 20 μ A/ $-$ 0.6 mA 20 μ A/ $-$ 0.6 mA		
$\overline{O}_0 - \overline{O}_7$	TRI-STATE Latch Outputs	150/40 (33.3)	-3 mA/24 mA (20 mA)		

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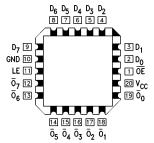
DDD D20M75 / Drinted in LL S. A.

Connection Diagrams

Pin Assignment for DIP, SOIC and Flatpak



Pin Assignment for LCC



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Functional Description

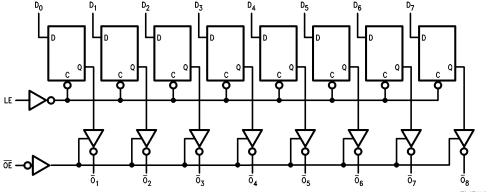
The 'F563 contains eight D-type latches with TRI-STATE output buffers. When the Latch Enable (LE) input is HIGH, data on the D_n inputs enters the latches. In this condition the latches are transparent, i.e., a latch output will change state each time its D input changes. When LE is LOW the latches store the information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE. The TRI-STATE buffers are controlled by the Output Enable (OE) input. When OE is LOW, the buffers are in the bi-state mode. When \overline{OE} is HIGH the buffers are in the high impedance mode but this does not interfere with entering new data into the latches.

Function Table

	Inputs		Internal	Output	Function		
ŌĒ	LE	D	Q	0			
Н	Χ	Х	Х	Z	High Z		
Н	Н	L	Н	Z	High Z		
Н	Н	Н	L	Z	High Z		
Н	L	Χ	NC	Z	Latched		
L	Н	L	н	Н	Transparent		
L	Н	Н	L	L	Transparent		
L	L	X	NC	NC	Latched		

- H = HIGH Voltage Level
- L = LOW Voltage Level X = Immaterial
 Z = High Impedance
 NC = No Change

Logic Diagram



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Please note that this diagram is provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

 $\begin{array}{lll} \text{Storage Temperature} & -65^{\circ}\text{C to} + 150^{\circ}\text{C} \\ \text{Ambient Temperature under Bias} & -55^{\circ}\text{C to} + 125^{\circ}\text{C} \\ \text{Junction Temperature under Bias} & -55^{\circ}\text{C to} + 175^{\circ}\text{C} \\ \text{Plastic} & -55^{\circ}\text{C to} + 150^{\circ}\text{C} \\ \end{array}$

V_{CC} Pin Potential to

Ground Pin -0.5V to +7.0V Input Voltage (Note 2) -0.5V to +7.0V Input Current (Note 2) -30 mA to +5.0 mA

Voltage Applied to Output in HIGH State (with $V_{CC} = 0V$)

 $\begin{array}{lll} \text{Standard Output} & -0.5 \text{V to V}_{\text{CC}} \\ \text{TRI-STATE Output} & -0.5 \text{V to } +5.5 \text{V} \end{array}$

Current Applied to Output

in LOW State (Max) twice the rated I_{OL} (mA)

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

Recommended Operating Conditions

Free Air Ambient Temperature

Supply Voltage

Military + 4.5V to + 5.5V Commercial + 4.5V to + 5.5V

DC Electrical Characteristics

Symbol	Parameter		54F/74F			Units	V _{CC}	Conditions		
Symbol	Faranie	tei	Min	Тур	Max	Onits	VCC	Conditions		
V _{IH}	Input HIGH Voltage		2.0			V		Recognized as a HIGH Signal		
V _{IL}	Input LOW Voltage				0.8	V		Recognized as a LOW Signal		
V _{CD}	Input Clamp Diode Vo	oltage			-1.2	V	Min	$I_{\text{IN}} = -18 \text{mA}$		
V _{OH}	Output HIGH 54F 10% V _{CC} Voltage 54F 10% V _{CC} 74F 10% V _{CC} 74F 10% V _{CC} 74F 5% V _{CC} 74F 5% V _{CC}		2.5 2.4 2.5 2.4 2.7 2.7			V	Min	$\begin{split} I_{OH} &= -1 \text{ mA} \\ I_{OH} &= -3 \text{ mA} \\ I_{OH} &= -1 \text{ mA} \\ I_{OH} &= -3 \text{ mA} \\ I_{OH} &= -1 \text{ mA} \\ I_{OH} &= -3 \text{ mA} \\ \end{split}$		
V _{OL}	Output LOW 54F 10% V _{CC} Voltage 74F 10% V _{CC}				0.5 0.5	٧	Min	$I_{OL} = 20 \text{ mA}$ $I_{OL} = 24 \text{ mA}$		
I _{IH}	Input HIGH 54F Current 74F				20.0 5.0	μΑ	Max	$V_{IN} = 2.7V$		
I _{BVI}	Input HIGH Current 54F Breakdown Test 74F				100 7.0	μΑ	Max	V _{IN} = 7.0V		
I _{CEX}	Output HIGH 54F Leakage Current 74F				250 50	μΑ	Max	V _{OUT} = V _{CC}		
V _{ID}	Input Leakage 74F		4.75			V	0.0	$I_{\text{ID}} = 1.9 \mu\text{A}$ All Other Pins Grounded		
l _{OD}	Output Leakage Circuit Current	74F			3.75	μΑ	0.0	V _{IOD} = 150 mV All Other Pins Grounded		
I _{IL}	Input LOW Current				-0.6	mA	Max	V _{IN} = 0.5V		
lozh	Output Leakage Current				50	μΑ	Max	V _{OUT} = 2.7V		
l _{OZL}	Output Leakage Current				-50	μΑ	Max	V _{OUT} = 0.5V		
los	Output Short-Circuit Current		-60		-150	mA	Max	V _{OUT} = 0V		
I _{ZZ}	Bus Drainage Test				500	μΑ	0.0V	V _{OUT} = 5.25V		
ICCL	Power Supply Current			40	61	mA	Max	$V_O = LOW$		
Iccz	Power Supply Curren	t		40	61	mA	Max	V _O = HIGH Z		

AC Electrical Characteristics

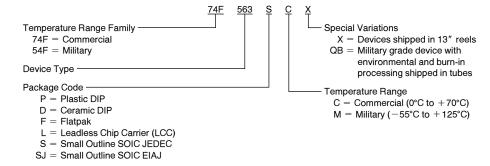
Symbol	Parameter				T _A , V _C	4F C = Mil 50 pF	74F T _A , V _{CC} = Com C _L = 50 pF		Units
		Min	Тур	Max	Min	Max	Min	Max	
t _{PLH} t _{PHL}	Propagation Delay D_n to \overline{O}_n	3.5 2.5		8.5 6.5	3.0 2.0	10.5 7.5	3.0 2.0	9.5 7.0	ns
t _{PLH} t _{PHL}	Propagation Delay LE to \overline{O}_n	4.5 3.0		9.5 7.0	4.0 2.5	11.0 7.5	4.0 2.5	10.5 7.0	ns
t _{PZH}	Output Enable Time	2.0 3.0		7.5 8.5	2.0 2.5	9.5 10.0	2.0 1.5	9.0 9.5	- ns
t _{PHZ}	Output Disable Time	1.5 1.5		5.5 5.5	1.5 1.5	7.0 5.5	1.5 1.5	6.5 5.5	

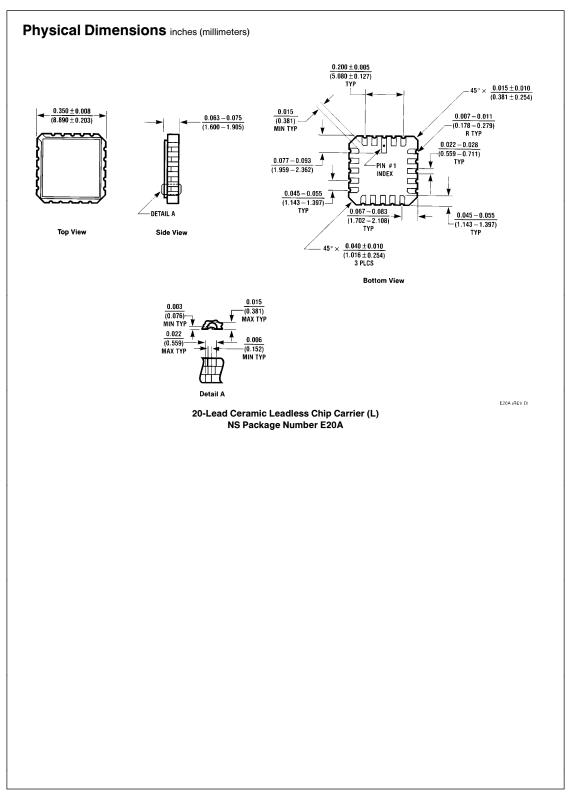
AC Operating Requirements

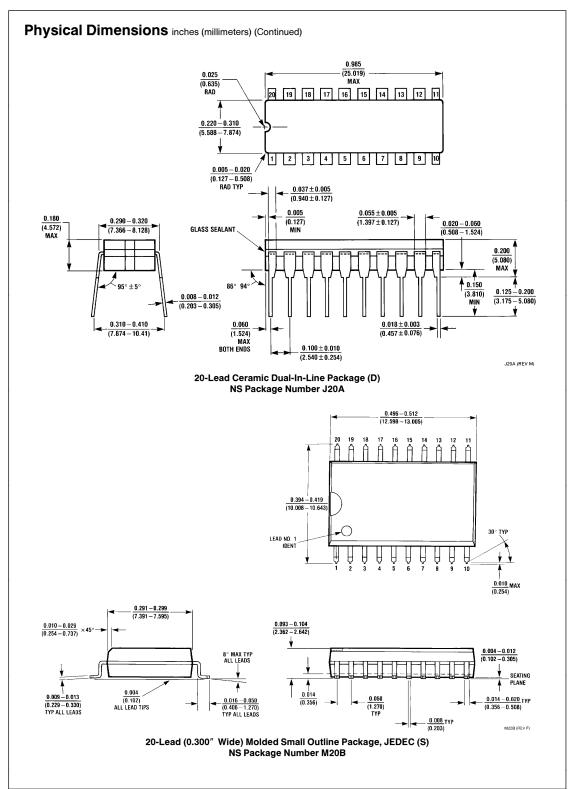
		$74F$ $T_A = +25^{\circ}C$ $V_{CC} = +5.0V$		54	ŀF	74F			
Symbol	Parameter			$T_A, V_{CC} = Mil$		T _A , V _{CC} = Com		Units	
		Min	Max	Min	Max	Min	Max]	
t _S (H)	Setup Time, HIGH or LOW D _n to LE	2.0 2.0		2.0 2.0		2.0 2.0		ns	
t _h (H)	Hold Time, HIGH or LOW D _n to LE	3.0 3.0		3.0 3.0		3.0 3.0		ns	
t _w (H)	LE Pulse Width, HIGH	4.0		4.0		4.0		ns	

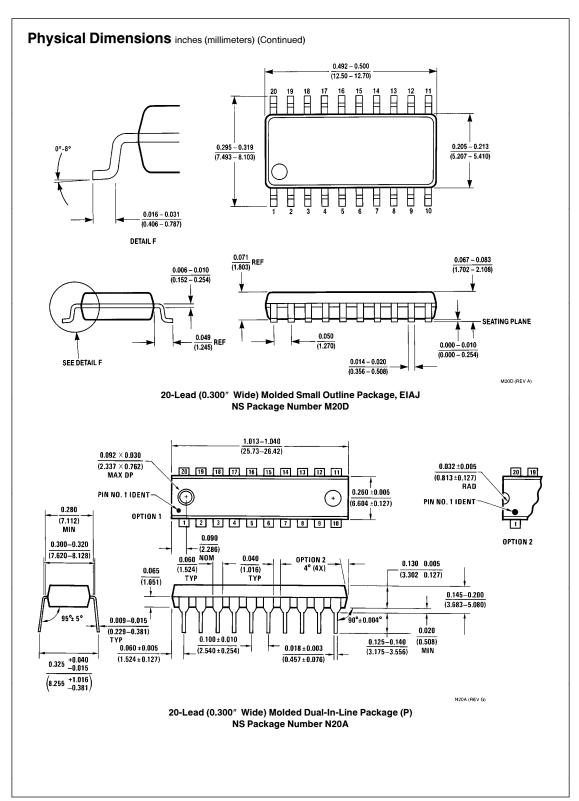
Ordering Information

The device number is used to form part of a simplified purchasing code where the package type and temperature range are defined as follows:

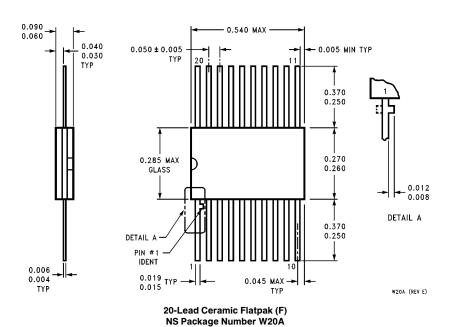








Physical Dimensions inches (millimeters) (Continued)



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